1. General description

Dual N-channel enhancement mode Field-Effect Transistor (FET) in a very small SOT363 (SC-88) Surface-Mounted Device (SMD) plastic package using Trench MOSFET technology.

2. Features and benefits

- · Very fast switching
- Low threshold voltage
- Trench MOSFET technology
- ESD protection up to 2 kV
- AEC-Q101 qualified

3. Applications

- Relay driver
- High-speed line driver
- · Low-side load switch
- · Switching circuits

4. Quick reference data

Table 1. Quick reference data

Symbol	Parameter	Conditions		Min	Тур	Max	Unit		
Per transistor	Per transistor								
V _{DS}	drain-source voltage	T _j = 25 °C		-	-	30	V		
V _{GS}	gate-source voltage			-8	-	8	V		
I _D	drain current	V _{GS} = 4.5 V; T _{amb} = 25 °C	[1]	-	-	350	mA		
Static characte	Static characteristics (per transistor)								
R _{DSon}	drain-source on-state resistance	$V_{GS} = 4.5 \text{ V}; I_D = 350 \text{ mA}; T_j = 25 \text{ °C}$		-	1	1.4	Ω		

^[1] Device mounted on an FR4 Printed-Circuit Board (PCB), single-sided copper, tin-plated, mounting pad for drain 1 cm².



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5. Pinning information

Table 2. Pinning information

Pin	Symbol	Description	Simplified outline	Graphic symbol
1	S1	source TR1		D1 D2
2	G1	gate TR1	654	
3	D2	drain TR2		G1
4	S2	source TR2	0	\\\\\\\\\\\\\\\\\\\\\\\\\\\\\\\\\\\\\\
5	G2	gate TR2	1 2 3	
6	D1	drain TR1	TSSOP6 (SOT363)	S1 S2 017aaa256

6. Ordering information

Table 3. Ordering information

Type number	Package				
	Name	Description	Version		
NX3008NBKS		plastic, surface-mounted package; 6 leads; 0.65 mm pitch; 2.1 mm x 1.25 mm x 0.95 mm body	SOT363		

7. Marking

Table 4. Marking codes

Type number	Marking code[1]
NX3008NBKS	LB%

[1] % = placeholder for manufacturing site code

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8. Limiting values

Table 5. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions		Min	Max	Unit
Per transist	or			<u> </u>	'	
V _{DS}	drain-source voltage	T _j = 25 °C		-	30	V
V _{GS}	gate-source voltage			-8	8	V
I _D	drain current	V _{GS} = 4.5 V; T _{amb} = 25 °C	[1]	-	350	mA
		V _{GS} = 4.5 V; T _{amb} = 100 °C	[1]	-	230	mA
I _{DM}	peak drain current	T_{amb} = 25 °C; single pulse; $t_p \le 10 \mu s$		-	1.4	Α
P _{tot}	total power dissipation	T _{amb} = 25 °C	[2]	-	280	mW
			[1]	-	320	mW
		T _{sp} = 25 °C		-	990	mW
Per device						
P _{tot}	total power dissipation	T _{amb} = 25 °C	[2]	-	445	mW
Tj	junction temperature			-55	150	°C
T _{amb}	ambient temperature			-55	150	°C
T _{stg}	storage temperature			-65	150	°C
Source-drai	n diode			1		
Is	source current	T _{amb} = 25 °C		-	300	mA
ESD maxim	um rating		'	'		'
V _{ESD}	electrostatic discharge voltage	НВМ	[3]	-	2000	V

- [1] Device mounted on an FR4 Printed-Circuit Board (PCB), single-sided copper, tin-plated, mounting pad for drain 1 cm².
- 2 Device mounted on an FR4 Printed-Circuit Board (PCB), single-sided copper, tin-plated and standard footprint.
- [3] Measured between all pins.

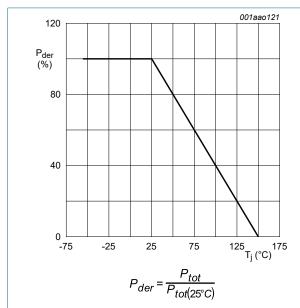


Fig. 1. Normalized total power dissipation as a function of junction temperature

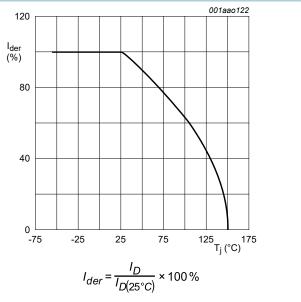
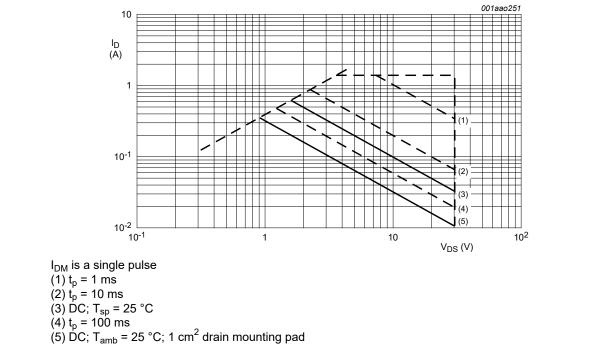


Fig. 2. Normalized continuous drain current as a function of junction temperature

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Safe operating area; junction to ambient; continuous and peak drain currents as a function of drain-Fig. 3. source voltage

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9. Thermal characteristics

Table 6. Thermal characteristics

Symbol	Parameter	Conditions		Min	Тур	Max	Unit
Per device							
$R_{th(j-a)}$	thermal resistance from junction to ambient	in free air	[1]	-	-	300	K/W
Per transist	or		,				
R _{th(j-a)}	thermal resistance from	in free air	[1]	-	390	445	K/W
	junction to ambient		[2]	-	340	390	K/W
R _{th(j-sp)}	thermal resistance from junction to solder point			-	-	130	K/W

- [1] Device mounted on an FR4 PCB, single-sided copper, tin-plated and standard footprint.
- [2] Device mounted on an FR4 PCB, single-sided copper, tin-plated, mounting pad for drain 1 cm².

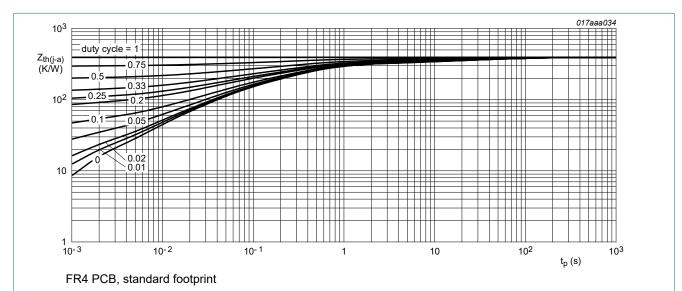


Fig. 4. Per transistor: Transient thermal impedance from junction to ambient as a function of pulse duration; typical values

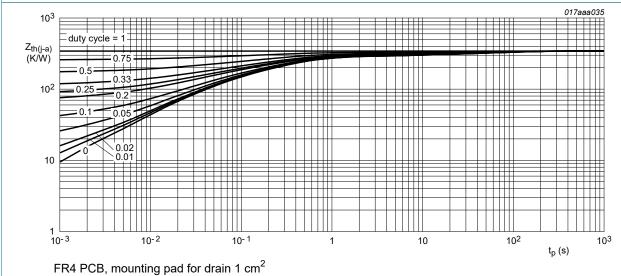


Fig. 5. Per transistor: Transient thermal impedance from junction to ambient as a function of pulse duration; typical values

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10. Characteristics

Table 7. Characteristics

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
Static chara	acteristics (per transistor)					
V _{(BR)DSS}	drain-source breakdown voltage	I _D = 250 μA; V _{GS} = 0 V; T _j = 25 °C	30	-	-	V
V_{GSth}	gate-source threshold voltage	$I_D = 250 \mu A; V_{DS} = V_{GS}; T_j = 25 \text{ °C}$	0.6	0.9	1.1	V
I _{DSS}	drain leakage current	V _{DS} = 30 V; V _{GS} = 0 V; T _j = 25 °C	-	-	1	μΑ
		V _{DS} = 30 V; V _{GS} = 0 V; T _j = 150 °C	-	-	10	μΑ
I _{GSS}	gate leakage current	V _{GS} = 8 V; V _{DS} = 0 V; T _j = 25 °C	-	0.2	1	μΑ
		V _{GS} = -8 V; V _{DS} = 0 V; T _j = 25 °C	-	0.2	1	μΑ
		V _{GS} = 4.5 V; V _{DS} = 0 V; T _j = 25 °C	-	10	-	nA
		V _{GS} = -4.5 V; V _{DS} = 0 V; T _j = 25 °C	-	10	-	nA
		V _{GS} = 2.5 V; V _{DS} = 0 V; T _j = 25 °C	-	1	-	nA
		$V_{GS} = -2.5 \text{ V}; V_{DS} = 0 \text{ V}; T_j = 25 \text{ °C}$	-	1	-	nA
R _{DSon}	drain-source on-state	V _{GS} = 4.5 V; I _D = 350 mA; T _j = 25 °C	-	1	1.4	Ω
	resistance	V _{GS} = 4.5 V; I _D = 350 mA; T _j = 150 °C	-	1.8	2.5	Ω
		V _{GS} = 2.5 V; I _D = 200 mA; T _j = 25 °C	-	1.4	2.1	Ω
		V_{GS} = 1.8 V; I_D = 10 mA; T_j = 25 °C	-	2	2.8	Ω
9 _{fs}	forward transconductance	$V_{DS} = 10 \text{ V}; I_D = 350 \text{ mA}; T_j = 25 \text{ °C}$	-	310	-	mS
Dynamic ch	naracteristics (per transist	or)		'		
Q _{G(tot)}	total gate charge	V _{DS} = 15 V; I _D = 350 mA; V _{GS} = 4.5 V;	-	0.52	0.68	nC
Q _{GS}	gate-source charge	T _j = 25 °C	-	0.17	-	nC
Q _{GD}	gate-drain charge		-	0.08	-	nC
C _{iss}	input capacitance	V _{DS} = 15 V; f = 1 MHz; V _{GS} = 0 V;	-	34	50	pF
C _{oss}	output capacitance	T _j = 25 °C	-	6.5	-	pF
C _{rss}	reverse transfer capacitance		-	2.2	-	pF
t _{d(on)}	turn-on delay time	$V_{DS} = 20 \text{ V}; R_L = 250 \Omega; V_{GS} = 4.5 \text{ V};$	-	15	30	ns
t _r	rise time	$R_{G(ext)} = 6 \Omega; T_j = 25 °C$	-	11	-	ns
t _{d(off)}	turn-off delay time		-	69	138	ns
t _f	fall time	1	-	19	-	ns
Source-dra	in diode (per transistor)		'	-	1	
V _{SD}	source-drain voltage	I _S = 350 mA; V _{GS} = 0 V; T _i = 25 °C	0.47	0.85	1.2	V

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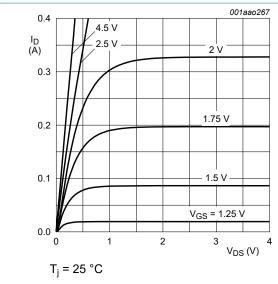
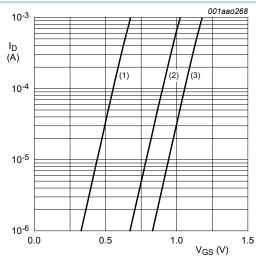


Fig. 6. Output characteristics: drain current as a function of drain-source voltage; typical values



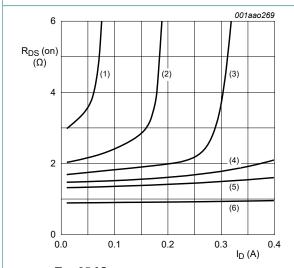
 $T_j = 25 \, ^{\circ}C; \, V_{DS} = 5 \, V$

(1) minimum values

(2) typical values

(3) maximum values

Fig. 7. Sub-threshold drain current as a function of gate-source voltage



 $T_j = 25 \, ^{\circ}C$

 $(1) V_{GS} = 1.5 V$

(2) $V_{GS} = 1.75 \text{ V}$

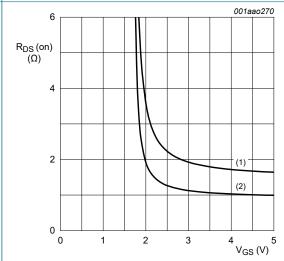
(3) $V_{GS} = 2.0 \text{ V}$

 $(4) V_{GS} = 2.25 V$

 $(5) V_{GS} = 2.5 V$

 $(6) V_{GS} = 4.5 V$

Fig. 8. Drain-source on-state resistance as a function of drain current; typical values



 $I_D = 350 \text{ mA}$

 $(1) T_j = 150 °C$

 $(2) T_j = 25 °C$

Fig. 9. Drain-source on-state resistance as a function of gate-source voltage; typical values

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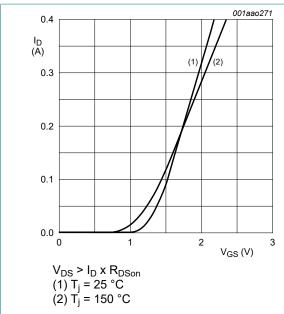


Fig. 10. Transfer characteristics: drain current as a function of gate-source voltage; typical values

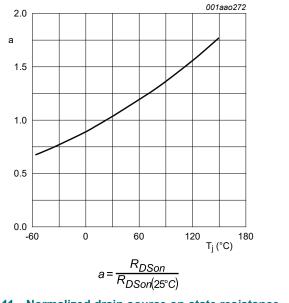
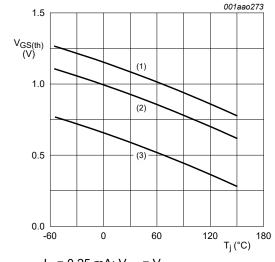


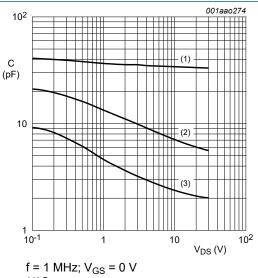
Fig. 11. Normalized drain-source on-state resistance as a function of junction temperature; typical values



 $I_D = 0.25 \text{ mA}; V_{DS} = V_{GS}$

- (1) maximum values
- (2) typical values
- (3) minimum values

Fig. 12. Gate-source threshold voltage as a function of junction temperature



 $(1)C_{iss}$

(2)C_{oss} (3)C_{rss}

Fig. 13. Input, output and reverse transfer capacitances as a function of drain-source voltage; typical values

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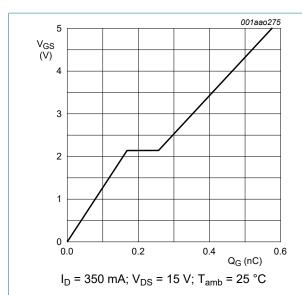


Fig. 14. Gate-source voltage as a function of gate charge; typical values

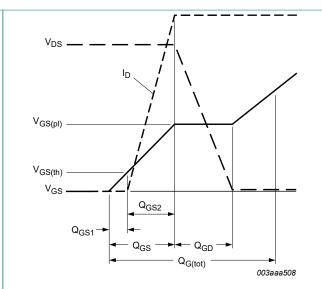
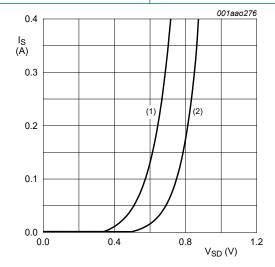


Fig. 15. Gate charge waveform definitions

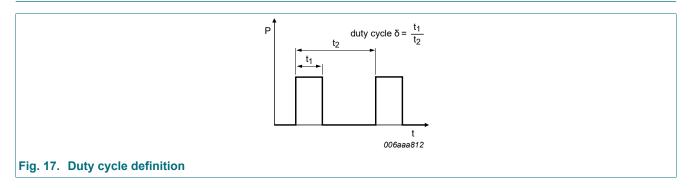


 $V_{GS} = 0 V$ (1) $T_j = 150 \,^{\circ}C$ (2) $T_j = 25 \,^{\circ}C$

Fig. 16. Source current as a function of source-drain voltage; typical values

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11. Test information



Quality information

This product has been qualified in accordance with the Automotive Electronics Council (AEC) standard *Q101 - Stress test qualification for discrete semiconductors*, and is suitable for use in automotive applications.

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12. Package outline

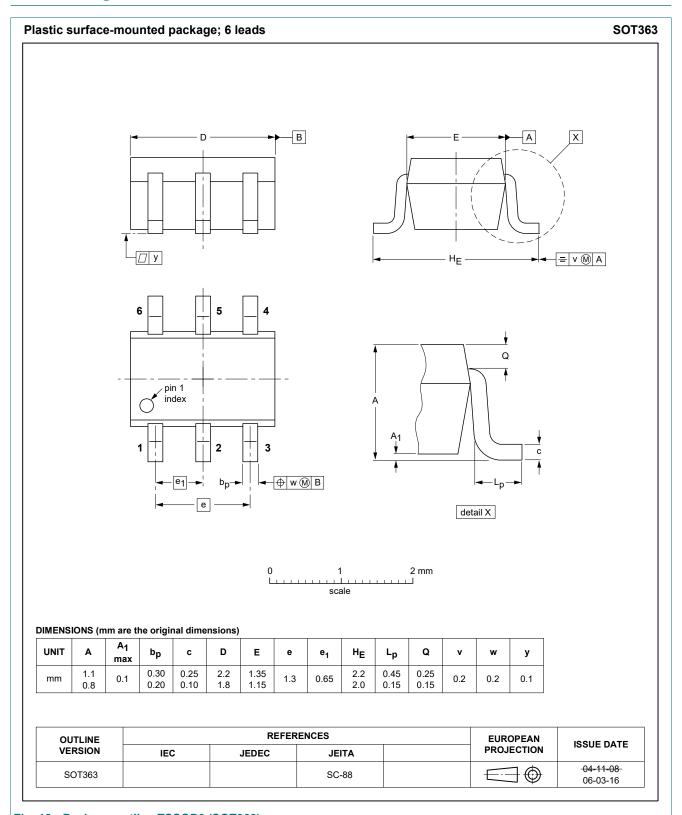
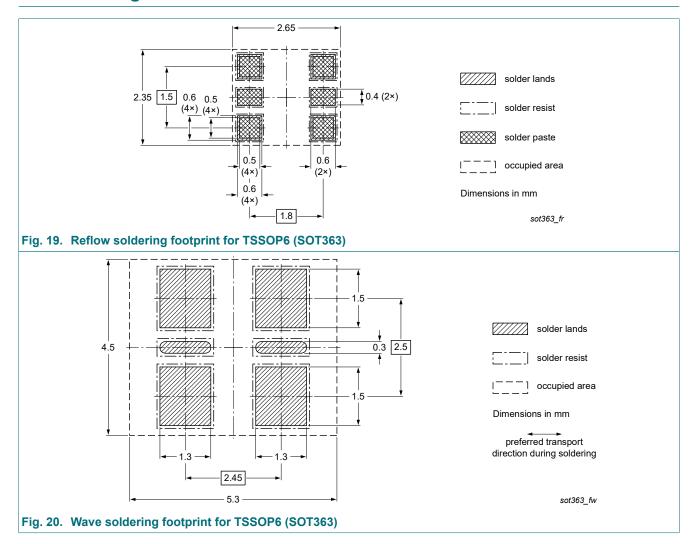


Fig. 18. Package outline TSSOP6 (SOT363)

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13. Soldering



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14. Revision history

Table 8. Revision history

······································								
Data sheet ID	Release date	Data sheet status	Change notice	Supersedes				
NX3008NBKS v.2	20221105	Product data sheet	-	NX3008NBKS v.1				
Modifications:	Chapter "Characteris	Chapter "Characteristics": typo correction, V _{SD} axis scaling for Fig. 16 revised						
NX3008NBKS v.1	20110801	Product data sheet	-	-				

15. Legal information

Data sheet status

Document status [1][2]	Product status [3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

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